NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI VMB70-12F** is Designed for

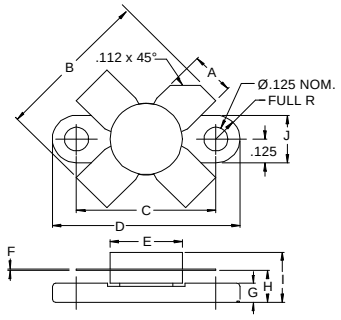
FEATURES:

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- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	12 A
V_{CBO}	36 V
V_{CEO}	18 V
V_{EBO}	3.5 V
P_{DISS}	183 W @ T_C = 25 ^{O}C
T_J	-65 ^{O}C to +200 ^{O}C
T_{STG}	-65 ^{O}C to +150 ^{O}C
θ_{JC}	1.05 ^{O}C/W

PACKAGE STYLE .380 4L FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.785 / 19.94	
C	.720 / 18.29	.730 / 18.54
D	.970 / 24.64	.980 / 24.89
E		.385 / 9.78
F	.004 / 0.10	.006 / 0.15
G	.085 / 2.16	.105 / 2.67
H	.160 / 4.06	.180 / 4.57
I		.280 / 7.11
J	.240 / 6.10	.255 / 6.48

ORDER CODE: ASI10745

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS					
BV_{CBO}	I_C = 50 mA		36			**V**
BV_{CES}	I_C = 100 mA		36			**V**
BV_{CEO}	I_C = 50 mA		18			**V**
BV_{EBO}	I_E = 10 mA		3.5			**V**
I_{CES}	V_{CE} = 12.5 V				10	**mA**
h_{FE}	V_{CE} = 5.0 V	I_C = 5.0 A	10		---	**---**
C_{OB}	V_{CB} = 12.5 V	f = 1.0 MHz			270	**pF**
P_G	V_{CE} = 12.5 V	P_{OUT} = 70 W f = 88 MHz	7.0			**dB**
η_C				60		**%**

Specifications are subject to change without notice.